L Number	Hits	Search Text	DB	Time stamp
1	1	"112'0965"	JP	2002/06/13 14:58
2	0	"jp11250965"	JP	2003/06/13 15:01
3	0	6433647.pn. and (sealing plate).clm.	JP	2003/06/13 15:01
4	0	6433647.pn. and (adhesive sealing plate).clm.	JP	2003/06/13 15:01
5	0	6433647.pn. and (sealing plate).clm.	USPAT	2003/06/13 15:01
6	1	6433647.pn.	USPAT	2003/06/13 15:53
7	0	patel-ashok.xp. and preffered adj embodiments	USPAT	2003/06/13 15:55
8	0	patel-ashok.xp. and preferred adj embodiments	USPAT	2003/06/13 15:52
-	229	(445/25).CCLS.	USPAT	2003/08/18 14:30
-	343	(313/512).CCLS.	USPAT	2003/08/18 14:34
-	0	09671654.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 14:33
-	1	9671654.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 14:33
-	229	(445/25).CCLS.	USPAT	2003/08/18 14:48
-	722	((313/512) or (445/25)).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 14:48
-	17	(((313/512) or (445/25)).CCLS.) and active adj matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 14:55
-	13	((((313/512) or 445/25)).CCLS.) and active adj matrix) and crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 14:56
-	1	((((313/512) or (445/25)).CCLS.) and active adj matrix) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 14:58
-	3	5672183.URPN.	USPAT	2003/08/18 14:57
-	1	((((313/512 or (445/25)).CCLS.) and active adj matrix) and (field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 15:01
-	0	(257.$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 15:01
-	134751	(25/.$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 15:02
-	66945	(31/.$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 15:02
-	8	((257/$).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 15:04

#	Query	Databases	Date
9	(257/59.ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:32
0	(313/9.ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:25
4347	((257/57) or (257/59) or (257/66) or (257/69) or (257/72) or (257/347) or (257/350)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 16:14
2	((257/57) or (257/59) or (257/66) or (257/69) or (257/72) or (257/347) or (257/350)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:36
4396	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 10:59
4178	yamazaki-shunpei.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/13 15:31
943	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT	2003/06/11 18:06
1171	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB	2003/08/13 15:32
0	(yamazaki-shunpei.in. or arai-yasuyuki.in.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/13 15:33
1	(yamazaki-shunpei.in. or arai-yasuyuki.in.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/13 15:33
2	10895%.URPN.	USPAT	2003/08/13 15:35
2	((257/57) or (257/59) or (257/66) or (257/69) or (257/72) or (257/347) or (257/350)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET nostft) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/13 16:15
5136	((257/57) or (257/59) or (257/66) or (257/69) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 13:56
2	(((257/57) or (257/59) or (257/66) or (257/69) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET nostft) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 16:15
2	("6188893" | "6246071").PN.	USPAT	2003/08/28 16:27
5150	((257/57) or (257/59) or (257/66) or (257/69) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:00

			USPAT;	2002/08/29 07:37
3	("6351010").PN.		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	("6153893" | "6246070").PN.		USPAT	2002/08/29 07:47
0	(("6153893" | "6246070").PN.) and organic		USPAT	2002/08/29 07:46
	with (EL electroluminescence			
	electroluminescent.			
0	(("6153893" | "6246070").PN.) and organic		USPAT	2002/08/29 07:46
	same (EL electroluminescence			
	electroluminescent			
3	semiconductor-energy-.laboratory.as.		USPAT	2002/08/29 07:43
4	semiconductor-energy-.laboratory.as.		USPAT;	2002/08/29 07:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	siny.as. and single adj crystal and active		USPAT;	2002/08/29 07:55
	adj matrix and gate with (FET field adj		US-PGPUB;	
	effect adj transistor)		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	siny.as. and single adj crystal and active		USPAT;	2002/08/29 08:00
	adj matrix and gate with (FET field adj		US-PGPUB;	
	effect adj transistor) and organic with		EPO; JPO;	
	(EL electroluminescent		DERWENT;	
	electroluminescence))		IBM_TDB	
0	siny.as. and single adj crystal and active		USPAT;	2002/08/29 08:00
	adj matrix and gate with (FET field adj		US-PGPUB;	
	effect adj transistor) and (organic with		EPO; JPO;	
	(EL electroluminescent		DERWENT;	
	electroluminescence)) and inert		IBM_TDB	
2	(((257/57) or (257/59) or (257/66) or		USPAT;	2002/08/29 08:38
	(257/66) or (257/72) or (257/347) or		US-PGPUB;	
	(257/350) or (313/512) or (445/25)).CCLS.)		EPO; JPO;	
	and active adj matrix and (organic with		DERWENT;	
	EL) and gate with (field adj effect adj		IBM_TDB	
	transistor FET) and single adj crystal			
2	(((257/57) or (257/59) or (257/66) or		USPAT;	2002/08/29 08:43
	(257/66) or (257/72) or (257/347) or		US-PGPUB;	
	(257/350) or (313/512) or (445/25)).CCLS.)		EPO; JPO;	
	and active adj matrix and (organic with		DERWENT;	
	(EL electroluminescence		IBM_TDB	
	electroluminescent)) and gate with (field			
	adj effect adj transistor FET) and single			
	adj crystal			
8	(((257/57) or (257/59) or (257/66) or		USPAT;	2002/08/29 08:44
	(257/66) or (257/72) or (257/347) or		US-PGPUB;	
	(257/350) or (313/512) or (445/25)).CCLS.)		EPO; JPO;	
	and active adj matrix and (organic with		DERWENT;	
	(EL electroluminescence		IBM_TDB	
	electroluminescent)) and gate with (field			
	adj effect adj transistor FET bottom adj			
	gate top adj gate) and single adj crystal			
8	(((257/57) or (257/59) or (257/66) or		USPAT;	2002/08/29 08:44
	(257/66) or (257/72) or (257/347) or		US-PGPUB;	
	(257/350) or (313/512) or (445/25)).CCLS.)		EPO; JPO;	
	and active adj matrix and (organic with		DERWENT;	
	(EL electroluminescence		IBM_TDB	
	electroluminescent)) and gate with (field			
	adj effect adj transistor FET bottom adj			
	gate top adj gate) and single adj crystal			
	and gas			

—	9	((((257/57) or (257/59) or (257/_8) or (257/_6) or (257/72) or (257/34_ or (_____56) or (313/512) or (445/__)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field a__ effect adj transistor FET b_ttom adj gate t_p adj gate) and single adj crystal and _inert adj ga_	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:17
—	80	((_____77) or (3_____) or (2_7 __) or (__7 __ or (25_____ or (25_____ or (___2__ or (313_512) or (445____)).CCLS.) and TFT with FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:25
—	1	6___-___.UPEN.	USPAT	2002/08/29 09:55
—	14	("5.4__9_"	"5____0_"	"54___4"	"____5"	"561____"	"56____"	"5___5"	"57___6"	"571___3"	"5__4414"	"5_8___"	"591____"	"___0135"	"56____3").PN.	USPAT	2002/08/29 09:56
—	0	(("5.__19(_	"5___2"	"541___2"	"__7___5"	"5___14"	"56____"	"5_43__6"	"5___55"	"571___"	"_____"	"_____"	"5__ __").PN. and active adj matrix and (organic with EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET b_ttom adj gate t_p adj gate) and single adj crystal and inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:59
—	0	(("5._ 120"	"5__05__"	"_401___" "55____"	"5____34"	"56___5"	"_5438_6"	"571____"	"571___5"	"__7___14"	"5_____"	"591____"	"__1___"	"___4_13".PN. and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate and single adj crystal and (inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:59
—	492	((((257/57) or (257/59) or (257/__) or (257/__) or (257/7_) or (25_/34__ or (__7/___) or (313/51_) or (445/__)).CCLS.) and inert gas with organic adj EL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:02
—	9	(((257/57) or (2__/59) or (257/6_ or (257/__) or (257/72) or (257/347 or (257/___) or (313/51_ or (445/__)).CCLS.) and inert adj gas with organic adj EL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:02
—	0	(((257 57) or (257/59) or (257/6_ or (__7/6_ or (25_/72_ or (257/347) or (___/__ or (313/512 or (445/__)).CCLS.) and inert adj gas with organic adj EL same oxidize	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:03
—	0	(((25_/57) or (2__/59) or (257/__) or (257/__ or (2__/7_) or (257/34_) or (___/35_ or (313/512) or (445/__)).CCLS.) and inert adj gas same organic adj EL same oxidize determinate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:03
—	0	((57/57) or (257/59) or (257/__) or (257/__) or (2__/7_) or (257/347 or (___/___ or (313/512) or (445/__)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and rare adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:20

2   (((257/57) or (257/59) or (257/66) or
     (257/66) or (257/) or (257/347) or
     (257/356) or (?1?/?1?) or (445/29)).CCLS.)
     and active adj matrix and (organic with
     (EL electroluminescence
     electroluminescent) and gate with (field
     adj effect adj transistor FET bottom adj
     gate tip adj gate and single adj crystal
     and helium he argon ar krypton kr xenon
     xe nitrogen n.   USPAT;   2002/08/29 10:21
                                                      US-PGPUB;
                                                      EPO; JPO;
                                                      DERWENT;
                                                      IBM_TDB

3   (((257/57) or (257/59) or (257/66) or
     (257/66) or (257/) or (257/347) or
     (257/356) or (?1?/?1?) or (445/)).CCLS.)
     and active adj matrix and (organic with
     (EL electroluminescence
     electroluminescent) and gate with (field
     adj effect adj transistor FET bottom adj
     gate tip adj gate) and single adj crystal
     and (helium he argon ar krypton kr xenon
     xe nitrogen n)   USPAT;   2002/08/29 10:24
                                                      EPO; JPO;
                                                      DERWENT;
                                                      IBM_TDB

3   (((257/57) or (257/59) or (257/66) or
     (257/66) or (257/71) or (257/347) or
     (257/356) or (313/511) or (445/)).CCLS.)
     and active adj matrix and (organic with
     (EL electroluminescence
     electroluminescent) and gate with (field
     adj effect adj transistor FET bottom adj
     gate tip adj gate) and single adj crystal   USPAT;   2002/08/29 11:12
                                                      EPO; JPO;
                                                      DERWENT;
                                                      IBM_TDB

3   (((257/57) or (257/59) or (257/66) or
     (257/66) or (257/71) or (257/347) or
     (257/356) or (313/511) or (445/15)).CCLS.)
     and active adj matrix and (organic with
     (EL electroluminescence
     electroluminescent) and gate with (field
     adj effect adj transistor FET bottom adj
     gate tip adj gate) and single adj crystal
) and (helium he argon ar krypton kr xenon
     xe nitrogen n.)   USPAT;   2002/08/29 10:26
                                                      EPO; JPO;
                                                      DERWENT;
                                                      IBM_TDB

3   (((257/57) or (257/59) or (257/66) or
     (257/66) or (257/71) or (257/347) or
     (257/356) or (313/511) or (445/15)).CCLS.)
     and active adj matrix and (organic with
     (EL electroluminescence
     electroluminescent)) and gate with (field
     adj effect adj transistor FET bottom adj
     gate tip adj gate) and single adj crystal
) and (helium he argon ar krypton kr xenon
     xe nitrogen n)   USPAT;   2002/08/29 10:27
                                                      EPO; JPO;
                                                      DERWENT;
                                                      IBM_TDB

1   (((257/57) or (257/59) or (257/66) or
     (257/66) or (257/71) or (257/347) or
     (257/356) or (313/511) or (445/15)).CCLS.)
     and active adj matrix and (organic with
     (EL electroluminescence
     electroluminescent) and gate with (field
     adj effect adj transistor FET bottom adj
     gate tip adj gate) and single adj crystal
) and (helium he argon ar krypton kr xenon
     xe nitrogen n) and (barium adj oxide
     silica adj gel drying)   USPAT;   2002/08/29 10:28
                                                      EPO; JPO;
                                                      DERWENT;
                                                      IBM_TDB

1   (((257/57) or (257/59) or (257/66) or
     (257/) or (257/) or (257/347) or
     (257/356) or (313/511) or (445/15)).CCLS.)
     and active adj matrix and (organic with
     (EL electroluminescence
     electroluminescent) and gate with (field
     adj effect adj transistor FET bottom adj
     gate tip adj gate) and single adj crystal
     and (helium he argon ar krypton kr xenon
     xe nitrogen n) and (helium he argon ar
     krypton kr xenon xe nitrogen n) and
     barium adj oxide silica adj gel drying)   USPAT;   2002/08/29 10:28
                                                      EPO; JPO;
                                                      DERWENT;
                                                      IBM_TDB

			USPAT;	2002/08/29 10:29
	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (415/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electr luminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen n)) and (helium he argon or krypton kr xenon xe nitrogen n inert adj gas inert adj gas) and (barium adj oxide silica adj gel drying)		EPO; JPO; DERWENT; IBM_TDB	
	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (415/25)).CCLS.) and active adj matrix and (organic with EL electroluminescence electr luminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon or krypton kr xenon xe nitrogen n)) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)		USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:14
	4	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal		USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:20
	1	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)		USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:15
	4	((257/57 or (257/59) or (257/347) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal		USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 14:12
	1075	313 3 4		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:58
	0	313/504,500		USPAT; US-PGPUB	2002/08/29 11:58
	1650	313 3 4 313 500		USPAT; US-PGPUB	2002/08/29 12:20
	1075	313 3 4		USPAT; US-PGPUB	2002/08/29 12:21
	1064	(313 504) or (313/500)).CCLS.		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:36

-	116	(((313/504) or (313/500)).CCLS.) AND Active adj matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:21
-	114	(((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:23
-	9	((((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet)) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 13:32
-	7	((((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet) and single adj crystal) and (inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:28
-	7	((((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet) and single adj crystal) and (inert adj gas rare adj gas helium he krypton or argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:36
-	0	20020074448.URPN.	USPAT	2001/08/29 12:36
-	810	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:37
-	530	((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:38
-	407	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium ne krypton kr argon ar xenon xe nitrogen) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:39
-	2	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium ne krypton or argon ar xenon xe nitrogen) same (envelope vacant vacancy) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:40
-	181	((313/504) or (313/500).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) and (organic adj EL organic adj layer) and (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:41
-	57	(((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:44
-	615	(((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:44
-	57	(((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer) and (inert adj gas rare adj gas helium ne krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:45
-	57	(((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 12:47

46	(((213/504) or (213/504)).CCLS.) and (organic adj EL organic adj layer)) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:33
10	(((((313/504) or (313/504)).CCLS.) AND Active adj matrix) and (field effect transistor fet) and (single adj crystal monocrystal monocrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:32
0	((((313/504) or (313/500)).CCLS.) AND Active adj matrix) and (field effect transistor fet) and (single adj crystal monocrystal monocrystalline) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:53
3	((((313/504) or (313/500)).CCLS.) AND Active adj) matrix) and (field effect transistor fet), and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 13:54
7008	(... or ... or (313/504) or (257/... or (257/... or 126/344) or (313/... or 313/... or 445/5) or (313/504) or (313/504) or (313/495)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TLB	2002/08/29 13:57
0	((...) or (257/59 or 257/66) or (257/... or 257/... or (257/317 or (313/... or (313/... or 445/5) or (313/504) or (313/504) or (313/495)).CCLS. and active adj matrix and (FET field adj effect adj transistor) same organic adj EL and (barium adj oxide silica adj and helium he nitrogen krypton kr argon ar xenon xe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:00
1	((257/... or (257/59) or (257/66) or (257/... or 257/... or (257/347 or (257/359) or (313/511) or 445/25) or (313/504) or (313/504) or (313/495)).CCLS. and active adj matrix and (FET field adj effect adj transistor) and organic adj EL and (barium adj oxide silica adj gel) and helium he nitrogen krypton kr argon ar xenon xe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:01
1	((257/... or (257/59) or (257/66) or (257/... or (257/... or (257/347) or (257/359) or (313/511) or 445/25) or (313/504) or (313/504) or (313/495)).CCLS. and active adj. matrix and (FET field adj effect adj transistor) and (organic with EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel) and helium he nitrogen krypton kr argon ar xenon xe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:03
1	((257/... or (257/59) or (257/66) or (257/... or (257/... or (257/347) or (257/... or (313/511) or 445/25) or (313/... or (313/504) or (313/495)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel) and helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:03

–	1	((257/57. or (257/59) or (257/66) or (257/6.) or (257/7.) or (257/347) or (257/3..) or (313/512) or 445/25) or (313/5.0) or (313/504) or (313/4.5)).CCLS.) and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel) and (helium he nitrogen krypton kr argon ar xenon xe	USPAT; US-PGPUB	2002/08/29 14:23
–	2	("6175186").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:04
–	24	(((57/57. or (257/59 or (257/66. or (257/6.. or (.57.7. or (257.347 or (257/360) or (313/51.. or 445/5 or (313/5.() or (313/.0.) or (313.445)).CCLS. and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:06
–	10	((.17/57 or (..7/5. or (.57/66 or ... or (.. or (.5. or (257.347) or 257/360) or (313/512) or 445/25) or (313/500) or (313/504) or (313/44..)).CCLS. and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:27
–	1	((257/57. or (257/59 or (257/66 or (257/66 or (257/71) or (257/347 or (257/360) or (313/512) or 445/25 or (313/50 or (313/504) or (313/445)).CCLS. and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and gopgel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:35
–	1	((257/57. or (257/59 or (257/66 or (257/66 or (257/71) or (257/347 or (257/360) or (313/512) or 445/25 or (313/50 or 313/504) or (313/445)).CCLS. and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel)	USPAT; US-PGPUB	2002/08/29 14:23
–	1	jp10294476	JP	2002/08/29 14:24
–	15	((257/57 or (..7. 5. or ... or (257/66 or (257/7.) or (257/347 or (257/360) or (313/512) or 445/25 or (313/50) or (313/504) or (313/445)).CCLS. and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:53
–	537	((.17/57 or (.57/59) or (257/66) or (.57/66 or (.57/7.) or (257/347) or (257/360) or (313/512) or 445/25) or (313/5.0) or (313/504) or (313/445)).CCLS.) and organic with (EL electroluminescent electroluminescence and (helium he nitrogen krypton kr argon ar xenon xe) and (barium oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:36

—	11	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or 445/25) or (313/504) or 313/504) or (313/495)).CCLS. and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (barium oxide silica adj gel) and google	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:41
—	0	jp10233065	JP	2002/08/29 14:42
—	0	semiconductor adj laboratory and yamazaki and "1998"	JP	2002/08/29 14:43
—	5179	yamazaki and "1998"	JP	2002/08/29 14:43
—	0	yamazaki and "1998" and semiconductor adj energy adj laboratory	JP	2002/08/29 14:43
—	0	10-233065 and yamazaki	JPO	2002/08/29 14:48
—	0	"10233065" and yamazaki	JP	2002/08/29 14:48
—	0	"10233065" and yamazaki	JP	2002/08/29 14:48
—	0	"jp10233065" and yamazaki	JP	2002/08/29 14:48
—	0	"jp10233065" and yamazaki	JP	2002/08/29 14:48
—	0	"jp10233065" and yamazaki	JP	2002/08/29 14:48
—	0	"jp10233065"	JP	2002/08/29 14:48
—	0	"jp10233065"	JP	2002/08/29 14:48
—	0	"jp1 233065"	JP	2002/08/29 14:48
—	368	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or 445/25) or (313/504) or 313/504) or (313/495)).CCLS. and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (barium oxide silica adj gel)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:50
—	83	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or 445/25) or (313/504) or 313/504) or (313/495)).CCLS. and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (barium adj oxide silica adj gel)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:51
—	36	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or 445/25) or (313/504) or (313/504) or (313/495)).CCLS. and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) same (barium adj oxide silica adj gel)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:52
—	3	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or 445/25) or (313/504) or (313/504) or (313/495)).CCLS. and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) same (barium adj oxide))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 14:55
—	7	("5739545" | "5747930" | "5834894" | "5837918" | "6046543" | "6246179" | "6307324").PN.	USPAT	2002/08/29 14:54
—	2	("6175186").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:13

–	3	(313/$ and ceramic with transparent).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:27
–	0	(313/$ and ceramic same transparent).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:27
–	0	(313/$ and ceramic same clear).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:27
–	66966	(313/$).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:27
–	0	((313/$).CCLS.) and nitride adj ceramic with (clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 15:28
–	359	((313/$).CCLS.) and ceramic with (clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 16:50
–	0	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and active adj matrix with goggle	USPAT	2002/08/29 15:54
–	24	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and display with goggle	USPAT	2002/08/29 15:59
–	0	jp11141163	JPO	2002/08/29 15:58
–	0	jp(11141163)	JPO	2002/08/29 15:58
–	26	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and display same goggle	USPAT	2002/08/29 15:59
–	26	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and display and goggle	USPAT	2002/08/29 16:46
–	9	nitride adj ceramic with (transparent clear)	USPAT	2002/08/29 16:47
–	0	nitride adj ceramic with oxide with glass with (transparent clear)	USPAT	2002/08/29 16:47
–	23	((313/$).CCLS.) and nitride adj ceramic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 16:52
–	0	((313/$).CCLS. and nitride adj ceramic same (transparent clear)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 16:51

–	20	/313/$).CCLS.) and nitride with ceramic same (display clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:07
–	0	jp1(2854476	JP	2002/08/29 17:07
–	0	jp12854476	JP	2002/08/29 17:07
–	0	jp0102854476	JP	2002/08/29 17:12
–	3	("6051010").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:13
–	0	("1459 and yamanaka and insulated adj gate").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:13
–	8	(((257/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/370) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and yamanaka and insulated adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:16
–	0	(((257/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/370) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and insulated adj gate and organic adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:17
–	2	sony.as. and insulated adj gate adj field and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 17:18
–	389	yamanaki-shunpei.in. or arai-yasuyuki.in.	US-PGPUB	2003/06/11 18:07
–	22	yamanaki-shunpei.in. and arai-yasuyuki.in.	US-PGPUB	2003/06/11 18:07
–	21	yamanaki-shunpei.in. and arai-yasuyuki.in. and organic	US-PGPUB	2003/06/12 11:17
–	0	"passivation film 847"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:56
–	0	"passivation film 847 is formed on the anode layer 846"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 11:01
–	0	"passivation film 847 is formed on the anode layer 846."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:57
–	1420	semiconductor adj device adj method adj fabricating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 11:00
–	745	semiconductor adj device adj method adj fabricating.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 11:01
–	0	"passivation film 847 is formed"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 11:02
–	0	yamazaki-shunpei.in. and arai-yasuyuki.in. and muakami-satoshi.in.	US-PGPUB	2003/06/12 11:18

–	1	yamazaki-shunpei.in. and arai-yasuyuki.in. and murakami-satoshi.in.	US-PGPUB	2003/06/12 11:18
–	2171	(313/512, or 313/504, or (313/500) or (345/84)).CCLS.	USPAT	2003/06/12 15:58
–	237	(OLED organic adj3 el adj3 (device display)).bi. and (fET field adj effect adj transistor).bi.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:07
–	315	(OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence).bi. and (fET field adj effect adj transistor).bi.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:08
–	166	(OLED organic adj3 el adj3 (device display) organic adj1 (electroluminescent electroluminescence).ki. and (fET field adj effect adj transistor).ki.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:08
–	98	((OLED organic adj3 el adj3 (device display) organic adj1 (electroluminescent electroluminescence).ki. and (fET field adj effect adj transistor.ki.) and (matrix matrices)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:09
–	52	(((fET organic adj3 el adj3 device display organic adj1 electroluminescent electroluminescence).ki. and (fET field adj effect adj transistor).ki. and matrix matrices) and (gas nitrogen krypton xenon argon neon helium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:16
–	36	((OLED organic adj3 el adj3 device display) organic adj1 electroluminescent electroluminescence).ki. and (fET field adj effect adj transistor).ki.) and matrix matrices); and (gas nitrogen krypton xenon argon neon helium) and (dry drying desiccant getter)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:27
–	36	US-6111553-$ or US-6115113-$ or US-6214510-$ or US-6104119-$ or US-6147471-$ or US-6140769-$ or US-6114109-$ or US-6114858-$ or US-6038710-$ or US-6075981-$ or US-6077540-$ or US-6445382-$ or US-6181415-$ or US-6075244-$ or US-6147151-$ or US-6028755-$ or US-6410261-$ or US-6413904-$ or US-6031560-$ or US-6316484-$ or US-6381010-$ or US-6246713-$ or US-6091116-$ or US-6091116-$ or US-6051015-$ or US-6115691-$).did. or US-6114115-$ or US-6015831-$ or US-6432140-$ or US-6482564-$ or US-6478715-$ or US-6429684-$ or US-6465834-$).did. or (EP-1089595-$).did. or (JP-2001167877-$).did. or (EP-1089595-$).did.	USPAT; EPO; JPO; DERWENT	2003/06/12 16:18

-	10	((US-6221553-$ or US-6219113-$ or US-[illegible]-$ or US-6184119-$ or US-[illegible]-$ or US-6140069-$ or US-[illegible]-$ or US-6[illegible]355[illegible]-$ or US-5[illegible]-$ or US-5[illegible]-$ or US-5[illegible]-$ or US-5[illegible]2-$ or US-6[illegible]-$ or US-6[illegible]44-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]4-$ or US-6[illegible]-$ or US-6[illegible]18-$ or US-6[illegible]-$ or US-6[illegible]116-$ or US-6[illegible]-$ or US-6[illegible]-$).did. or (US-6[illegible]15-$ or US-6[illegible]1-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]4-$).did. or (EP-108[illegible]595-$).did. or (JP-2001167877-$).did. or (EP-1[illegible]5-$).did.) and (silicon si) adj4 substrate	USPAT; EPO; JPO; DERWENT	2003/06/12 16:19
-	10	((US-6221553-$ or US-6219113-$ or US-6214[illegible]-$ or US-6184119-$ or US-6187[illegible]-$ or US-614[illegible]-$ or US-6114[illegible]-$ or US-6[illegible]-$ or US-[illegible]-$ or US-[illegible]-$ or US-[illegible]-$ or US-544[illegible]-$ or US-6[illegible]44[illegible]-$ or US-6270444-$ or US-6[illegible]-$ or US-6[illegible]355[illegible]-$ or US-641[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]4-$ or US-6[illegible]-$ or US-634[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$ or US-6[illegible]-$).did. or (US-6[illegible]4[illegible]15-$ or US-6[illegible]1-$ or US-6[illegible]-$ or US-64[illegible]-$ or US-64[illegible]-$ or US-64[illegible]4-$ or US-6[illegible]4-$).did. or (EP-1083595-$).did. or (JP-2001167877-$).did. or (EP-1[illegible]5-$).did.) and (silicon si) adj4 substrate	USPAT; EPO; JPO; DERWENT	2003/06/12 16:51
-	2	(((US-6221553-$ or US-6219113-$ or US-6214[illegible]-$ or US-6184119-$ or US-6187[illegible]7-$ or US-614[illegible]-$ or US-6114[illegible]-$ or US-6[illegible]55[illegible]-$ or US-5[illegible]-$ or US-5[illegible]81-$ or US-5[illegible]4[illegible]-$ or US-544[illegible]-$ or US-6[illegible]4[illegible]-$ or US-6[illegible]44-$ or US-6[illegible]-$ or US-6[illegible]55-$ or US-64[illegible]1-$ or US-64[illegible]-$ or US-6[illegible]-$ or US-6[illegible]64-$ or US-6[illegible]-$ or US-634[illegible]-$ or US-6191116-$ or US-6[illegible]116-$ or US-6[illegible]-$ or US-6[illegible]-$).did. or (US-6[illegible]15-$ or US-6[illegible]31-$ or US-64[illegible]-$ or US-64[illegible]84-$ or US-64[illegible]10-$ or US-64[illegible]594-$ or US-6[illegible]4-$).did. or (EP-108[illegible]595-$).did. or (JP-2001167877-$).did. or (EP-1[illegible]95-$).did.) and (silicon si) adj4 substrate) and (gas nitrogen krypton xenon argon neon helium).lm.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 19:01
-	2	610[illegible].pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:44
-	1	610[illegible].pn.	USPAT; EPO; JPO; IBM_TDB	2003/06/12 17:56

	36	((US-6221553-$ or US-6219113-$ or US-6117200-$ or US-6194119-$ or US-6...197-$ or US-614.309-$ or US-6...99-$ or US-610.558-$ or US-5...0-$ or US-590.191-$ or US-5...0-$ or US-544.32-$ or US-6...44.0-$ or US-6...44-$ or US-6...77-$ or US-6...35-$ or US-6...1-$ or US-643...9-$ or US-6...0-$ or US-6...64-$ or US-6...19-$ or US-6...18-$ or US-6...116-$ or US-6...116-$ or US-6...17-$ or US-613194-$).did. or US-6...15-$ or US-6..1831-$ or US-6441191-$ or US-6441764-$ or US-6465715-$ or US-6413584-$ or US-6417174-$).did. or EP-1084595-$).did. or US-20116787-$).did. or EP-1199545-$).did. and organic with (el electroluminescent electroluminescence)	USPAT; EPO; JPO; DERWENT	2003/06/12 16:52
	10	((US-6221553-$ or US-6219113-$ or US-6194119-$ or US-6194119-$ or US-6117197-$ or US-614...09-$ or US-6...4-$ or US-6...8-$ or US-5...0-$ or US-5...1-$ or US-6...34-$ or US-6...44-$ or US-6...44415-$ or US-6...444-$ or US-6...132-$ or US-6115595-$ or US-6...1-$ or US-6...94-$ or US-6...59-$ or US-6...64-$ or US-6...13-$ or US-6...18-$ or US-6...116-$ or US-6...116-$ or US-6...15-$ or US-6...94-$).did. or US-6...4115-$ or US-6...831-$ or US-6...190-$ or US-6465764-$ or US-6465715-$ or US-6413584-$ or US-6...74-$).did. or EP-1084595-$).did. or US-20116787-$).did. or EP-1199545-$).did. and (silicon si) adj4 substrate and organic with (el electroluminescent electroluminescence)	USPAT; EPO; JPO; DERWENT	2003/06/12 17:54
	31357	alumina with ceramic	USPAT; EPO; JPO; DERWENT	2003/06/12 17:55
	9698	alumina adj3 ceramic	USPAT; EPO; JPO; DERWENT	2003/06/12 17:55
	13	alumina adj3 ceramic and ((313/512) or (313/504 or (313/50 or (445/24)).CCLS.)	USPAT; EPO; JPO; DERWENT	2003/06/12 17:54
	1	6103515.pn. and silicon adj3 substrate	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:31
	4	identity-kosan-co-ltd.as. and active adj matrix and silicon with substrate	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:32
	4	identity-kosan-co-ltd.as. and active adj matrix and silicon with substrate and gas	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:42
	0	identity-kosan-co-ltd.as. and active adj matrix and silicon with (crystal crystalline) with substrate and gas	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:34
	4	identity-kosan-co-ltd.as. and active adj matrix and silicon with substrate and gas	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:43
	0	identity-kosan-co-ltd.as. and active adj matrix and silicon adj substrate and gas	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:43
	2	identity-kosan-co-ltd.as. and active adj matrix and silicon adj layer and gas	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:45

_	2	idemitsu-kosan-co-ltd.as. and active adj matrix and silicon adj layer and gas and (tft fet field adj effect adj transistor)	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:47
_	33	canon-kabushiki-kaisha.as. and active adj matrix and silicon adj layer and gas and (tft fet field adj effect adj transistor)	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:49
_	12	canon-kabushiki-kaisha.as. and active adj matrix and (single cry tal crystalline) near7 silicon adj3 layer and gas and (tft fet field adj effect adj transistor)	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:49
	0	canon-kabushiki-kaisha.as. and active adj matrix and (single crystal crystalline) near7 silicon adj3 layer and gas and (tft fet field adj effect adj transistor) and organic and (el electroluminescent electroluminesce).	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:50
	0	canon-kabushiki-kaisha.as. and active adj matrix and (single crystal crystalline) near7 silicon adj3 layer and gas and (tft fet field adj effect adj transistor) and organic and (el electroluminescent electroluminesce)	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:53
_	2	tdk-corporation.as. and active adj matrix and (single crystal crystalline) near7 silicon adj3 layer and gas and (tft fet field adj effect adj transistor) and organic and (el electroluminescent electroluminesce)	USPAT; EPO; JPO; IBM_TDB	2003/06/12 18:53
_	4	6.384 l2.TTPN.	USPAT	2003/06/12 18:59
_	76	US-4363674-$ or US-3665128-$ or (long list of US patent numbers) ... EP-1393945-$).did.	USPAT; US-PGPUB; EPO	2003/06/12 19:00
_	1	US-?-53345-$).did.	UJOCR	2003/06/12 19:00

57   ((US-6363664-$ or US-3665238-$ or
       US-6210915-$ or US-4204121-$ or
       US-5766053-$ or US-5883464-$ or
       US-5997578-$ or US-6037110-$ or
       US-6062532-$ or US-6424042-$ or
       US-6150416-$ or US-6380951-$ or
       US-6350110-$ or US-6150111-$ or
       US-6350118-$ or US-6356060-$ or
       US-6443561-$ or US-6170300-$ or
       US-5189655-$ or US-5566560-$ or
       US-5061364-$ or US-5771510-$ or
       US-5831137-$ or US-5664242-$ or
       US-5518165-$ or US-5909451-$).did. or
       (US-6272552-$ or US-6117158-$ or
       US-6406490-$ or US-6284241-$ or
       US-6307041-$ or US-6337201-$ or
       US-6093374-$ or US-6051711-$ or
       US-6064612-$ or US-6356464-$ or
       US-6601660-$ or US-6127924-$ or
       US-6461149-$ or US-6095245-$ or
       US-6317056-$ or US-6438141-$ or
       US-6169790-$ or US-5767116-$ or
       US-6507411-$ or US-5076621-$ or
       US-5119451-$ or US-5288272-$ or
       US-5374428-$ or US-6411018-$ or
       US-6161671-$ or US-6111121-$ or
       US-6439442-$).did. or (US-6514700-$ or
       US-6530921-$ or US-6500009-$ or
       US-6761439-$ or US-6462010-$ or
       US-6461463-$ or US-6448711-$ or
       US-6497121-$ or US-6369107-$ or
       US-6139167-$ or US-6411019-$ or
       US-5961461-$ or US-6480719-$).did. or
       (US-20010068131-$ or US-20010017643-$ or
       US-20010074939-$ or US-20020074746-$ or
       US-20010046579-$ or US-20010050532-$ or
       US-20030018911-$ or US-20020045397-$ or
       US-20010050785-$).did. or
       (EP-1199595-$ .did.) and organic

24   ((US-6283664-$ or US-3665233-$ or
      US-4?? -15-$ or US-4204701-$ or
      US-1?.. 53-$ or US-5683404-$ or
      US-1?.. 478-$ or US-6031110-$ or
      US-6??. 32-$ or US-6424042-$ or
      US-6?? 6(6-$ or US-6380509-$ or
      US-6?? 10-$ or US-6150011-$ or
      US-6?? ?9-$ or US-6456?4-$ or
      US-6413?50-$ or US-6?75?44-$ or
      US-6?? 305-$ or US-5685?4-$ or
      US-5?? 164-$ or US-5?513?1-$ or
      US-5811??-$ or US-5?64204-$ or
      US-5?5?61-$ or US-5209441-$).did. or
      US-6??2558-$ or US-6104?18-$ or
      US-64.?93-$ or US-6?6434?-$ or
      US-6?12?641-$ or US-6?3?44?-$ or
      US-6?43974-$ or US-6?617?4-$ or
      US-6?4470?-$ or US-6555?6?-$ or
      US-6?6?466-$ or US-4127?2?-$ or
      US-4??6143-$ or US-5?065141-$ or
      US-5?17?7?-$ or US-5436?41-$ or
      US-5?46079?-$ or US-6?5671?4-$ or
      US-6?? ???1-$ or US-5?07404?-$ or
      US-?.41?4-$ or US-6?18??1-$ or
      US-6??6?26-$ or US-6?4???? -$ or
      US-6??6??71-$ or US-6?11140-$ or
      US-6?494428-$).did. or US-6?1?700-$ or
      US-6?7?-21-$ or US-65??1?-$ or
      US-6?1?233-$ or US-646?1??-$ or
      US-6?2246?-$ or US-6448?1?-$ or
      US-6?1?61??-$ or US-6369?6?-$ or
      US-6?40167-$ or US-6411??-$ or
      US-5?41?6?-$ or US-6489?1?-$).did. or
      (US-200?0063101-$ or US-200?0?17643-$ or
      US-2??1??04935-$ or US-20120?4746-$ or
      US-2?01?046579-$ or US-20110??0532-$ or
      US-2??1?018911-$ or US-2020046397-$ or
      US-200?0?50785-$).did. or
      (EP-1?04535-$ .did.) and organic) and (tft
      fiel? adj effect adj3 transistor fet)

USPAT;   2003/06/12 19:01
US-PGPUB;
EPO; JPO;
DERWENT;
IBM_TDB

18 ?((((US-6383664-$ or US-3669236-$ or
US-6210915-$ or US-4204721-$ or
US-576????-$ or US-5883404-$ or
US-599????-$ or US-6037710-$ or
US-606????-$ or US-6424042-$ or
US-635????-$ or US-6380562-$ or
US-655????-$ or US-603????-$ or
US-625????-$ or US-635????-$ or
US-644????-$ or US-6?????-$ or
US-518????-$ or US-55?????-$ or
US-565????-$ or US-5???562-$ or
US-5811177-$ or US-486????-$ or
US-5???161-$ or US-5906??-?-$).did. or
((US-6370558-$ or US-610??58-$ or
US-6426591-$ or US-60?????-$ or
US-60?????-$ or US-655????-$ or
US-60?????-$ or US-6551?29-$ or
US-6?54???-$ or US-6355???-$ or
US-6?41???-$ or US-4107792-$ or
US-4?6?140-$ or US-?0?514?-$ or
US-5017???-$ or US-548????-$ or
US-5???678-$ or US-6757125-$ or
US-5??9???-$ or US-507????-$ or
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US-6?????-?-$).did. or US-651?700-$ or
US-6??????-?-$ or US-65?????-$ or
US-6???????-$ or US-6460???-$ or
US-646????-$ or US-6418710-$ or
US-64?6111-$ or US-6360???-$ or
US-6?44???-$ or US-6411???-$ or
US-5??????-$ or US-6483?19-$).did. or
?US-2002?653?1-$ or US-2002?017643-$ or
US-?????07493?-$ or US-?0?20064746-$ or
US-????046579-$ or US-2??2050532-$ or
US-?0?????8911-$ or US-20?20045397-$ or
US-20020050785-$).did. or
?EP-1039345-$).did.) and organic) and (tft
field adj effect adj3 transistor fet)) and
(gas nitrogen krypton xenon argon neon
helium)

USPAT;   2003/06/12 19:02
EPO; JPO;
DERWENT;
IBM_TDB

13 ?((US-6363664-$ or US-3665231-$ or
    US-6210815-$ or US-4204721-$ or
    US-5766053-$ or US-1383464-$ or
    US-5997378-$ or US-6037710-$ or
    US-606?632-$ or US-6424092-$ or
    US-635?416-$ or US-6780568-$ or
    US-6?5?210-$ or US-615?087-$ or
    US-635??--$ or US-?56022-$ or
    US-6441?4?-$ or US-61??086-$ or
    US-6168967-$ or US-6585695-$ or
    US-56612?4-$ or US-77?1562-$ or
    US-541??77-$ or US-186420?-$ or
    US-54?6?4?-$ or US-?909(?1-$).did. or
     US-633?568-$ or US-61?0848-$ or
    US-6420991-$ or US-?8436?-$ or
    US-60?2?41-$ or US-?5?7?F8-$ or
    US-?5?6???4-$ or US-?5501?04-$ or
    US-65?4?7?1-$ or US-655006?-$ or
    US-?5?1666-$ or US-430??6?-$ or
    US-49?0144-$ or US-50?5246-$ or
    US-53170?6-$ or US-?43?041-$ or
    US-5?8??2?-$ or US-57671?6-$ or
    US-??1?201-$ or US-50?8644-$ or
    US-???1??-$ or US-1?84?41-$ or
    US-???1?4-$ or US-?41?088-$ or
    US-6?8??7?-$ or US-611?6??-$ or
    US-?48-4?7-$).did. or (US-651?700-$ or
    US-61?0?4?-$ or US-620?079-$ or
    US-?6??7??-$ or US-646?4??0-$ or
    US-?4?347?-$ or US-6448700-$ or
    US-?450???-$ or US-6369617-$ or
    US-?040141-$ or US-641120?-$ or
    US-5?4?76?-$ or US-?439710-$).did. or
    (US-?00??0691?1-$ or US-100.0017643-$ or
    US-?001?07492?-$ or US-?002.084746-$ or
    US-15.1?146570-$ or US-20010050532-$ or
    US-?001?0018011-$ or US-2002?045397-$ or
    US-?0010?50784-$).did. or
    (EP-1?0948-$?.did. and organic) and (tft
    field ad? effect ad?3 transistor fet)) and
    (nitrogen krypton xenon argon neon helium)

USPAT;   2003/06/12 19:02
EPO; JPO;
DERWENT;
IBM_TDB

76 US-6551724-$ or US-6538374-$ or
US-6537656-$ or US-6139941-$ or
US-6512939-$ or US-6422079-$ or
US-651?8?1-$ or US-??19766-$ or
US-61?4?9-$ or US-6?8?71?-$ or
US-644?4??-$ or US-645246?-$ or
US-643?71?-$ or US-64??6?-$ or
US-64??2??-$ or US-64?6?41-$ or
US-641?0??-$ or US-41?079-$ or
US-63??66?-$ or US-??????1-$ or
US-6???61?-$ or US-6????5?-$ or
US-6351?1?-$ or US-6??1441-$ or
US-62?94?6-$ or US-6?????-$).did. or
US-6??1??6-$ or US-6??9?69-$ or
US-60?44??-$ or US-6194?1?-$ or
US-51?4?6-$ or US-5?78654-$ or
US-6?1???1-$ or US-411?79?-$ or
US-6?61?6?-$ or US-6?51010-$ or
US-61036??-$ or US-566?1?4-$ or
US-5661???-$ or US-5?79?0?-$ or
US-51?9415-$ or US-5611177-$ or
US-57?156?-$ or US-5?67?7?6-$ or
US-5446???-$ or US-60??7?7-$ or
US-?36?????-$ or US-?30?0?1-$ or
US-?????1?-$ or US-???????1-$ or
US-??????-$ or US-?11?1?0-$ or
US-??1?6??-$).did. or (US-5636790-$ or
US-64?6?41-$ or US-??1???6-$ or
US-5?9?4??-$ or US-4????1??-$ or
US-4???1?-$ or US-46?6???-$ or
US-5??7464-$ or US-?06???2-$ or
US-??9?17?-$ or US-576?0?3-$ or
US-43?0?56-$ or US-?15018?-$).did. or
(US-?0?0016911-$ or US-20010017643-$ or
US-?0020045397-$ or US-?0020074938-$ or
US-?00?007474?-$ or US-?0020063191-$ or
US-?00?0130785-$ or US-?010046579-$ or
US-?0010050?3?-$).did. or
(EP-10?0?95-$).did.
1 (US-37?9445-$).did.

USPAT;   2003/06/13 11:53
US-PGPUB;
EPO

USOCR   2003/06/13 11:53

Search History   6/13/0? ?:57:25 PM   Page 21
C:\APPS\east\workspaces\09-71654.wsp

9   ((US-6551724-$ or US-6508374-$ or
    US-6481686-$ or US-6526441-$ or
    US-xxxxxxx-$ or US-6520079-$ or
    US-xxxxxxx-$ or US-6513700-$ or
    US-xxxxx4x-$ or US-6587xxx-$ or
    US-xxxxxxx-$ or US-6460xxx-$ or
    US-xxxxxxx-$ or US-6413xxx-$ or
    US-xxxxxxx-$ or US-6411xxx-$ or
    US-xxxxxx4-$ or US-xx84xx7-$ or
    US-xxxxxx5-$ or US-xx8660x0-$ or
    US-xxxxxxx-$ or US-xx84xxx-$ or
    US-xxxxxxx-$ or US-xx76016-$).did. or
    (US-6541746-$ or US-6555x69-$ or
    US-xx84x7x-$ or US-6183903-$ or
    US-6111211-$ or US-6078xx4-$ or
    US-xxxxx11-$ or US-6127702-$ or
    US-xx7xxxx-$ or US-6351010-$ or
    US-6139644-$ or US-6801344-$ or
    US-6009640-$ or US-6039018-$ or
    US-615441x-$ or US-5611137-$ or
    US-5171647-$ or US-5757116-$ or
    US-5844414-$ or US-4957710-$ or
    US-xxxxxxx-$ or US-5xxxx1-$ or
    US-xxxxxx1-$ or US-xx84xxx-$ or
    US-xxxxxx1-$ or US-5686790-$ or
    US-4844x41-$ or US-5x11136-$ or
    US-5195146-$ or US-4918144-$ or
    US-4x247.1-$ or US-5075128-$ or
    US-5x82484-$ or US-5140442-$ or
    US-6447178-$ or US-5766413-$ or
    US-6060468-$ or US-6151137-$).did. or
    US-20010018011-$ or US-20010017643-$ or
    US-2010045307-$ or US-20010014938-$ or
    US-2010038471x-$ or US-2010058191-$ or
    US-2010060785-$ or US-2010046579-$ or
    US-2001050531-$).did. or
    EP-10490193-$).did.) and (insulated
    insulating) adj3 gate

1   6413467.pn.

2   64x94x7.pn. 6555969.pn.

0   (6423447.pn. 6555969.pn.) and (field adj
    effect tft)

2   6434447.pn. 6555969.pn.) and (tft)

63870 6434447.pn. 6555969.pn.) and single adj
    61 18x1.PN. crystal crystalline) with
    silicon si

0   6431497.pn. 6555969.pn.) and single adj5
    (crystal crystalline) with silicon si)

88 tft with insulated adj gate adj field adj
    effect adj transistor

2   (6434447.pn. 6555969.pn. and (tft) and
    pixel adj portion

2   (6434447.pn. 6555969.pn.) and (tft) same
    pixel adj portion

2   (6413487.pn. 6555969.pn.) and (crystal
    crystalline) with (silicon si)

–	44186	/313/\$.CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/13 12:55
–	66840	(313/\$.CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/13 12:55
	0	((31 /\$.CCLS.) and tft with insulated adj gate or field adj effect adj transistor	USPAT; EPO; JPO; IBM_TDB	2003/06/13 12:56
–	464	tft same single adj4 (crystal crystaline) adj4 silicon.	USPAT; EPO; JPO; IBM_TDB	2003/06/13 12:57
–	279	tft with single adj4 (crystal crystaline) adj4 silicon.	USPAT; EPO; JPO; IBM_TDB	2003/06/13 12:58
	1	6433467.pn.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/13 13:06
–	8	("5641xxx" | "5711304" | "5834893" | "538xxxx" | "5891264" | "5953x62" | "605xxxx" | "624xxxx".PN.	USPAT	2003/06/13 13:05
	3	("564xxxx" | "5711304" | "5834893" | "5381741" | "5891264" | "5953x62" | "605xxxx" | "624xxx ".PN.) and tft and gas	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/13 13:07
–	10	((US-xxx1724-\$ or US-x55x874-\$ or US-x537x6x-\$ or US-xx2891x-\$ or US-xx2x49x-\$ or US-x5x2079-\$ or US-x5x3x1-\$ or US-x318x7x-\$ or US-x14x4x-\$ or US-x482710-\$ or US-x4x147x-\$ or US-x46x4xx-\$ or US-x44571x-\$ or US-x441551-\$ or US-x12xx1x-\$ or US-x42x54x-\$ or US-x417513-\$ or US-x411014-\$ or US-x3x3x24-\$ or US-x3x5x17-\$ or US-x35x4x6-\$ or US-x35x010-\$ or US-x2x1x8-\$ or US-xx44340-\$ or US-x210-1x-\$ or US-x175135-\$).did. or (US-x5x7x46-\$ or US-x55x069-\$ or US-xxx4x7x-\$ or US-5168901-\$ or US-51141x4-\$ or US-5x7x834-\$ or US-5xxx2x1x-\$ or US-41x7042-\$ or US-x372559-\$ or US-x361x10-\$ or US-x1x3x5x-\$ or US-5xx1364-\$ or US-5xx5x9x-\$ or US-x154128-\$ or US-514x4x5-\$ or US-xx11x7x-\$ or US-x7715x1-\$ or US-x7571x8-\$ or US-5xx4366-\$ or US-x43771x-\$ or US-xxxx7x-\$ or US-5x0x81x-\$ or US-xxx7x1-\$ or US-xx44167-\$ or US-xxx1xx1x-\$ or US-x11130x-\$ or US-x4x4xx-\$).did. or (US-5x82790-\$ or US-544xx71-\$ or US-54139x4-\$ or US-x1x145x-\$ or US-4xx-11x-\$ or US-4x04x11-\$ or US-x66x2x-\$ or US-x9x447x-\$ or US-x06x7x1-\$ or US-x4x7x8-\$ or US-x764xxx-\$ or US-x34xxx8-\$ or US-x15xxx-\$).did. or (US-2xxx018911-\$ or US-xxxxxx17643-\$ or US-xxxxx45397-\$ or US-10200x4933-\$ or US-xxxxx13474x-\$ or US-x020068191-\$ or US-xxxx5078x-\$ or US-x010046579-\$ or US-xxxxx60532-\$).did. or (EP-1xxx9x-\$).did.) and (tft) and single adjx crystal crystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/13 13:18

–	2	(6433487.pn. 6555969.pn.) and (tft) and single adj3 (crystal crystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/13 13:20
–	2	(6433487.pn. 6555969.pn.) and (tft) and single adj3 (crystal crystalline) and semiconductor adj2 film with (si silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/13 13:22
–	2	(6433487.pn. 6555969.pn.) and active adj matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/13 14:58